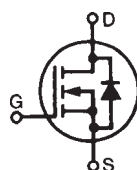


# Polar™ Power MOSFET

## HiPerFET™

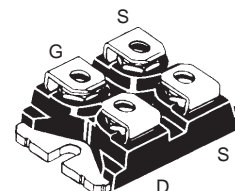
# IXFN64N50P

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



$V_{DSS} = 500V$   
 $I_{D25} = 50A$   
 $R_{DS(on)} \leq 85m\Omega$   
 $t_{rr} \leq 200ns$

miniBLOC, SOT-227 B  
 E153432



G = Gate                      D = Drain  
 S = Source

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	500	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	500	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	50	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	150	A
$I_A$	$T_C = 25^\circ C$	64	A
$E_{AS}$	$T_C = 25^\circ C$	2.5	J
$dV/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	20	V/ns
$P_D$	$T_C = 25^\circ C$	625	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS	$t = 1min$ 2500	V~
	$I_{ISOL} \leq 1mA$	$t = 1s$ 3000	V~
$M_d$	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
<b>Weight</b>		30	g

### Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500 V~
- Fast Intrinsic Diode
- Avalanche Rated
- Low  $R_{DS(on)}$

### Advantages

- Low Gate Drive Requirement
- High Power Density

### Applications:

- Switched-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ$			25 $\mu A$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 32A$ , Note 1			85 m $\Omega$

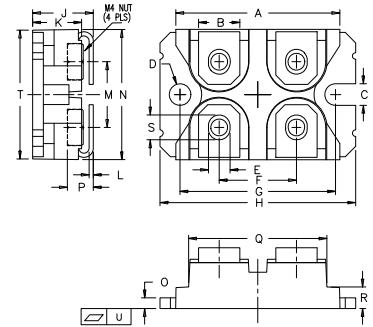
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20V, I_D = 32A$ , Note 1	30	50	S
$C_{iss}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		9700	nF
$C_{oss}$			970	pF
$C_{rss}$			30	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 32A$ $R_G = 2\Omega$ (External)		30	ns
$t_r$			25	ns
$t_{d(off)}$			85	ns
$t_f$			22	ns
$Q_{g(on)}$	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 32A$		150	nC
$Q_{gs}$			50	nC
$Q_{gd}$			50	nC
$R_{thJC}$			0.20	$^{\circ}C/W$
$R_{thCS}$		0.05		$^{\circ}C/W$

### Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0V$			64 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			250 A
$V_{SD}$	$I_F = 64A, V_{GS} = 0V$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25A, -di/dt = 100A/\mu s$ $V_R = 100V$			200 ns
$Q_{RM}$			0.6	$\mu C$
$I_{RM}$			6.0	A

Note 1: Pulse Test,  $t \leq 300\mu s$ ; Duty Cycle,  $d \leq 2\%$ .

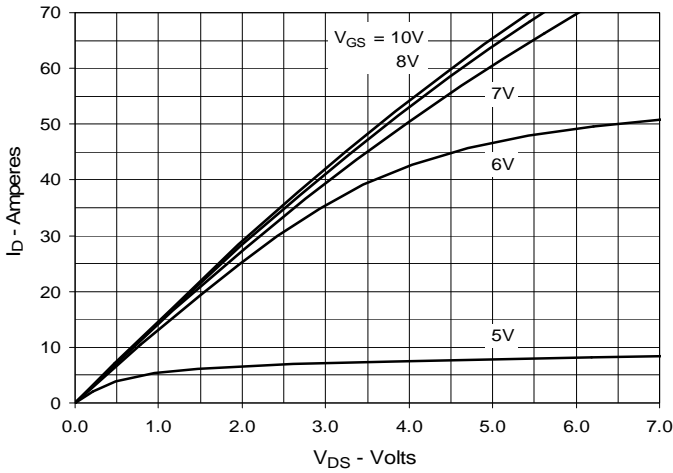
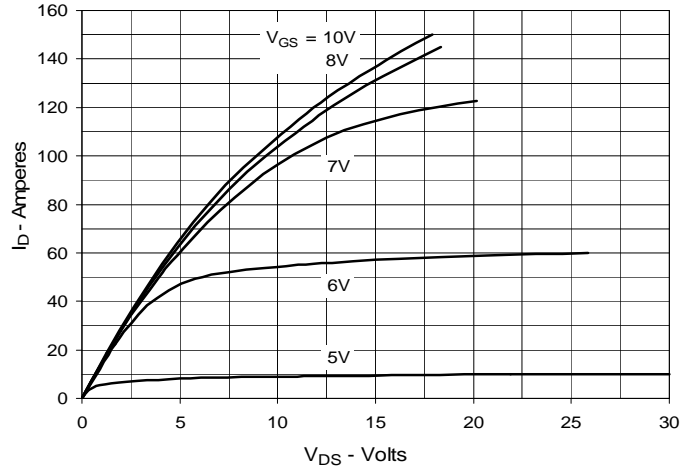
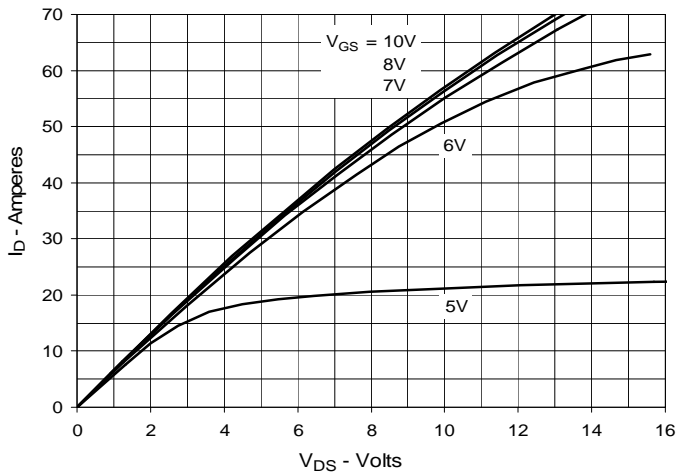
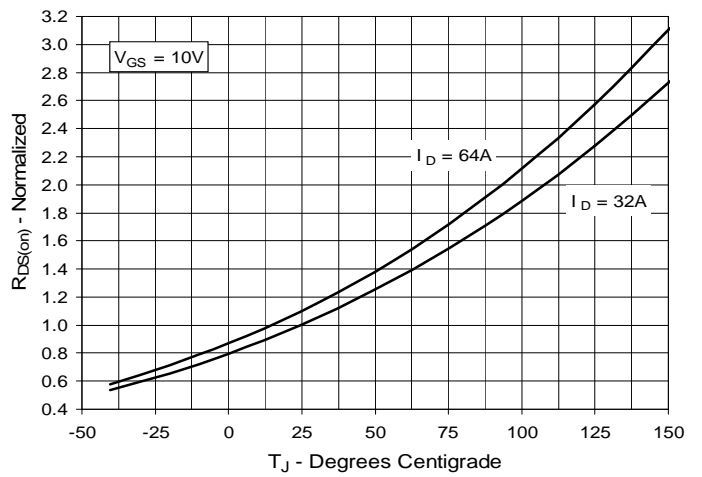
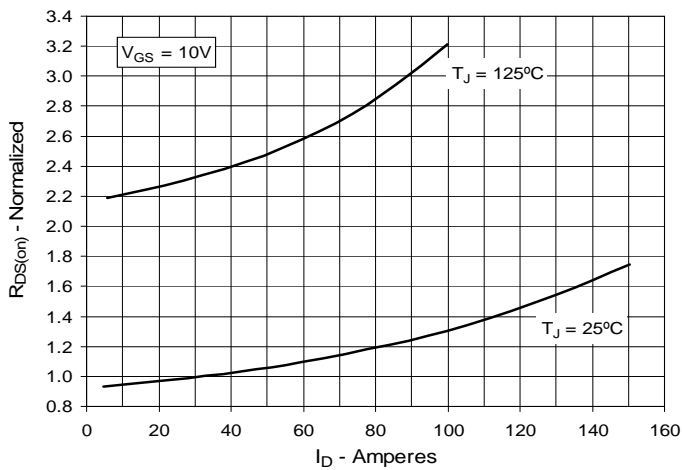
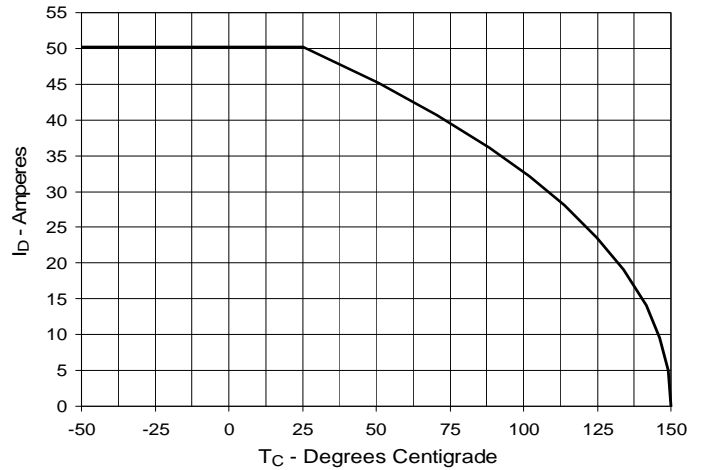
### SOT-227B Outline



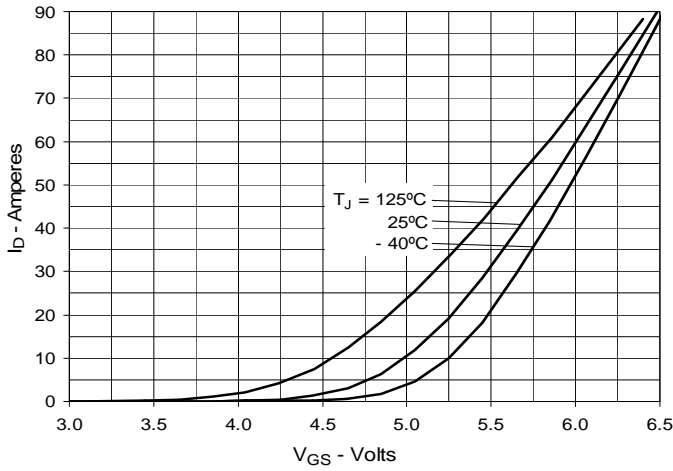
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

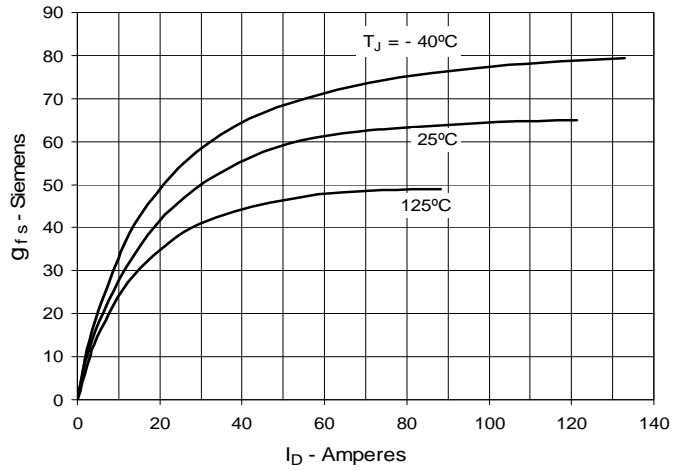
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics  
@ 25°C**

**Fig. 2. Extended Output Characteristics  
@ 25°C**

**Fig. 3. Output Characteristics  
@ 125°C**

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 32A$  Value  
vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 32A$  Value  
vs. Drain Current**

**Fig. 6. Maximum Drain Current vs.  
Case Temperature**


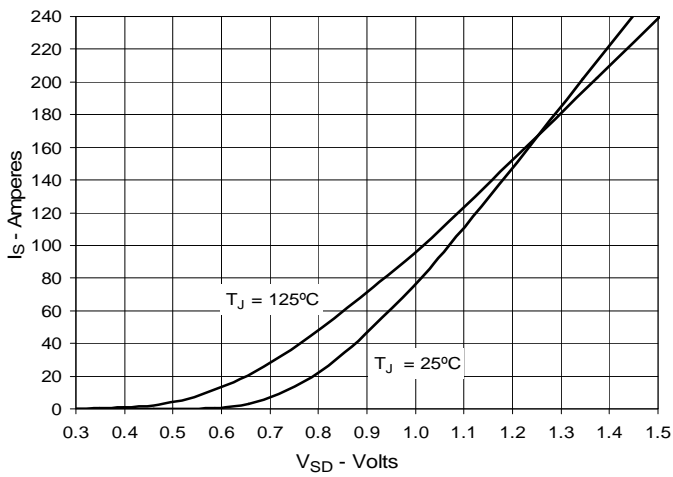
**Fig. 7. Input Admittance**



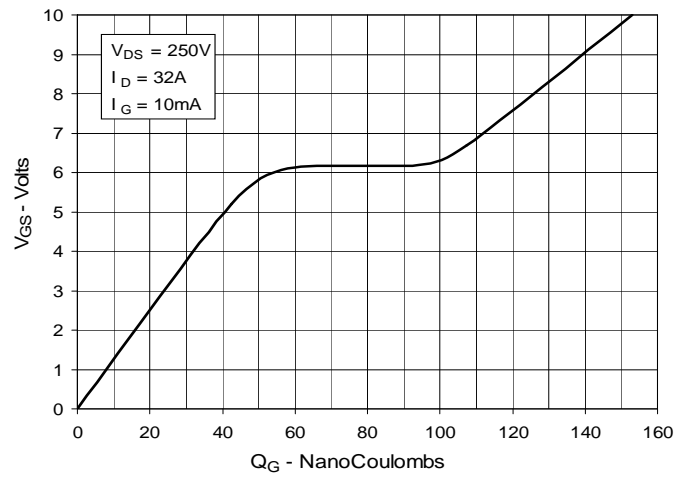
**Fig. 8. Transconductance**



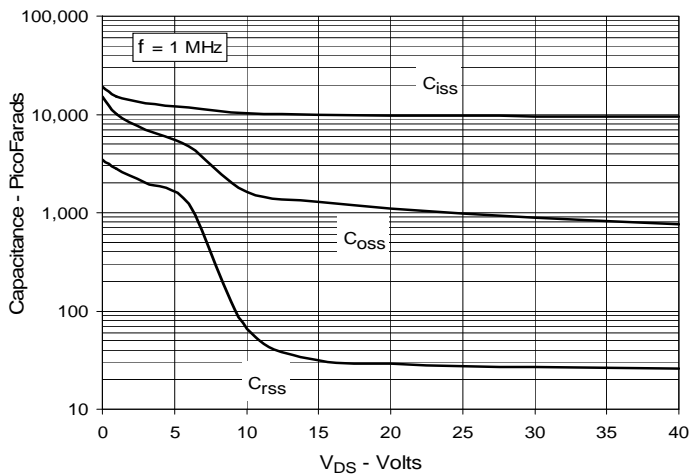
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



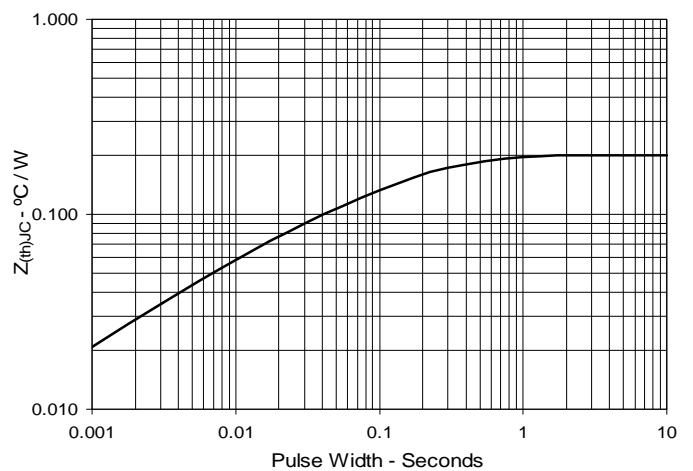
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**





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